

ABSTRACT OF THE DISCLOSURE

1 A semiconductor device including an IGFET (insulated gate field effect transistor)
2 (30) is disclosed. IGFET (30) may include a source/drain area (15) having an impurity
3 concentration distribution that may be formed shallower at a higher concentration than the
4 impurity concentration distribution in another source/drain area (7). A gate oxide film may
5 include a first gate oxide film (5) adjacent to source/drain area (7) and a second gate oxide
6 film (12) adjacent to source drain area (15). Second gate oxide film (12) may be thinner than
7 first gate oxide film (5). An impurity concentration distribution of a second channel impurity
8 area (11) under second gate oxide film (12) may be at a higher concentration than an
9 impurity concentration distribution of a first channel impurity area (9) under first gate oxide
10 film (5). In this way, an electric field at a PN junction of source/drain area (7) may be
11 reduced.